



US009299950B2

(12) **United States Patent**
Song et al.

(10) **Patent No.:** **US 9,299,950 B2**
(45) **Date of Patent:** **Mar. 29, 2016**

(54) **ORGANIC LIGHT EMITTING DISPLAY APPARATUS**

USPC 313/500, 504-505; 257/40, 88, 99,
257/E33.066, 433, 734; 438/29, 27, 82, 99
See application file for complete search history.

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(*) Notice: Subject to any disclaimer, the term of this
patent is extended or adjusted under 35
U.S.C. 154(b) by 142 days.

(21) Appl. No.: **14/071,001**

(22) Filed: **Nov. 4, 2013**

(65) **Prior Publication Data**

US 2014/0367651 A1 Dec. 18, 2014

(30) **Foreign Application Priority Data**

Jun. 18, 2013 (KR) 10-2013-0069955

(51) **Int. Cl.**
H01L 27/32 (2006.01)
H01L 51/52 (2006.01)

(52) **U.S. Cl.**
CPC **H01L 51/525** (2013.01); **H01L 51/5221**
(2013.01); **H01L 51/5228** (2013.01)

(58) **Field of Classification Search**
CPC H01L 27/3244; H01L 27/3276; H01L
27/3288; H01L 51/5234; H01L 51/524;
H01L 51/5243; H05K 1/189; H05K
2201/10128

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(57) **ABSTRACT**

An organic light emitting display apparatus includes a lower substrate and an upper substrate. The lower substrate includes a light emitting device having an organic emission layer between first and second electrodes, and an auxiliary electrode under and electrically connected to the second electrode. The upper substrate includes an embossing member contacting the second electrode. The embossing member is coupled to the upper substrate to face the lower substrate and applies a pressure to establish an electrical connection between the auxiliary electrode and the second electrode.

21 Claims, 6 Drawing Sheets

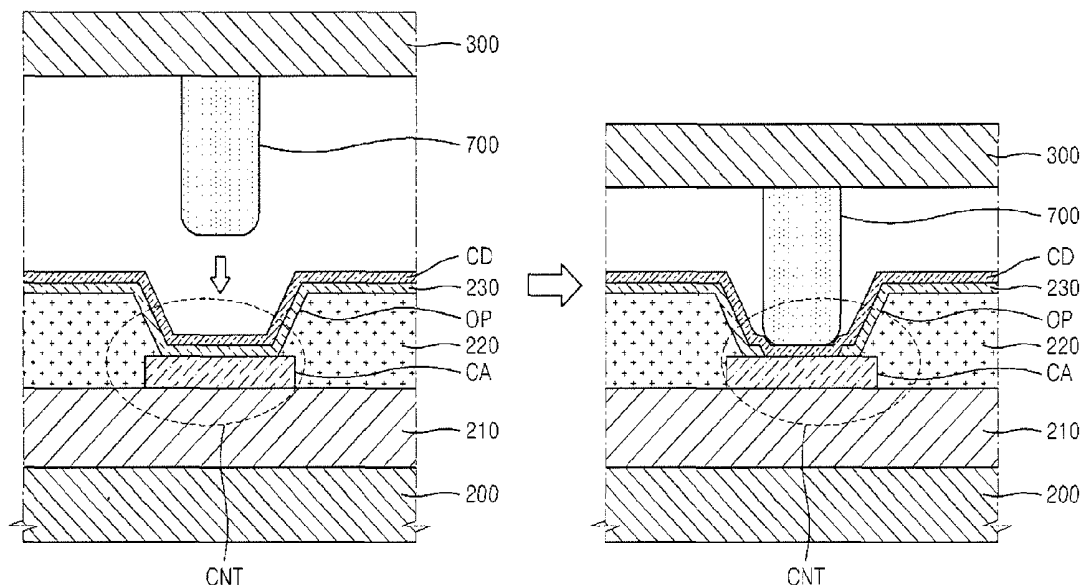


FIG. 1

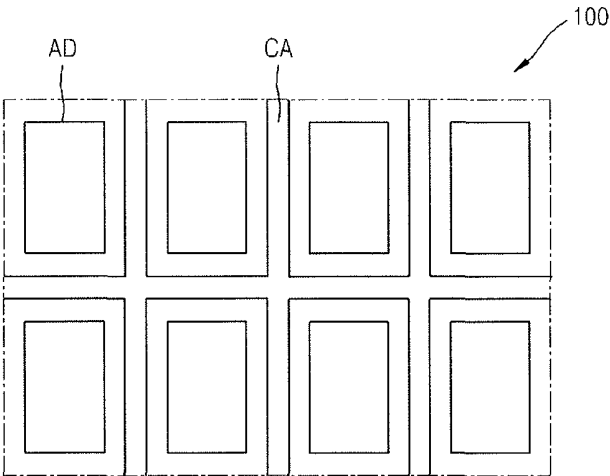


FIG. 2

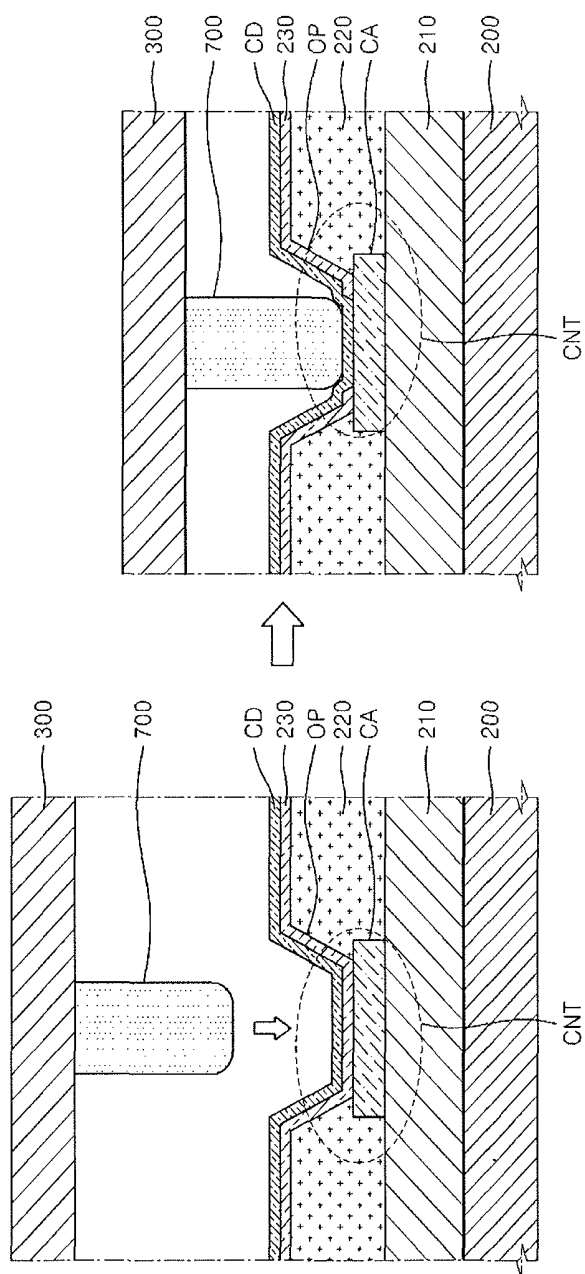


FIG. 3

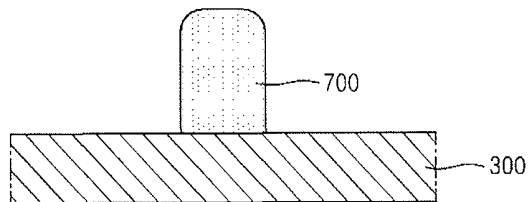


FIG. 4

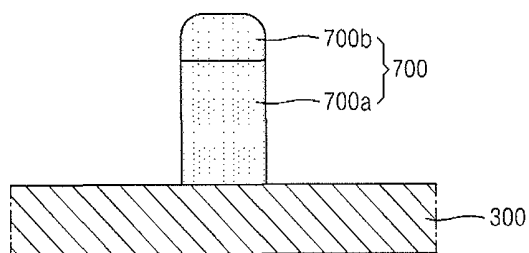


FIG. 5

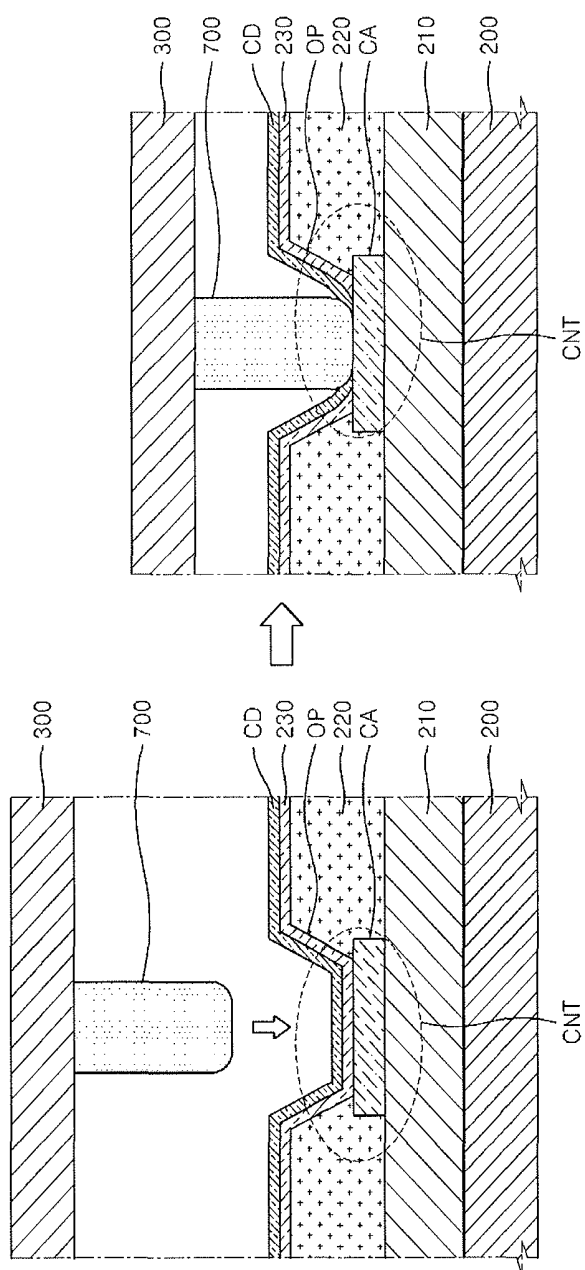


FIG. 6

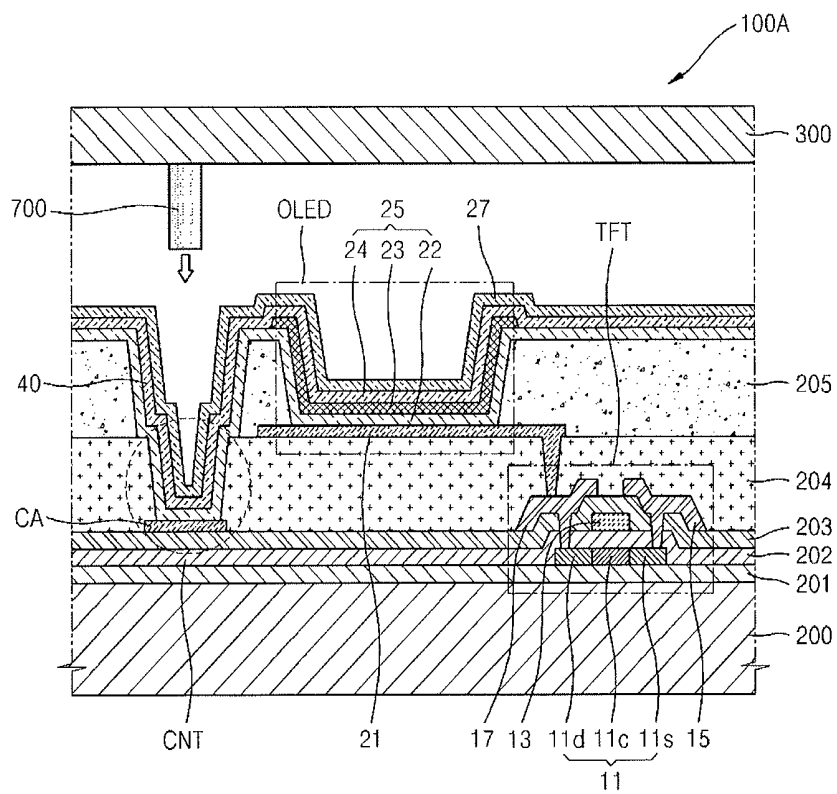
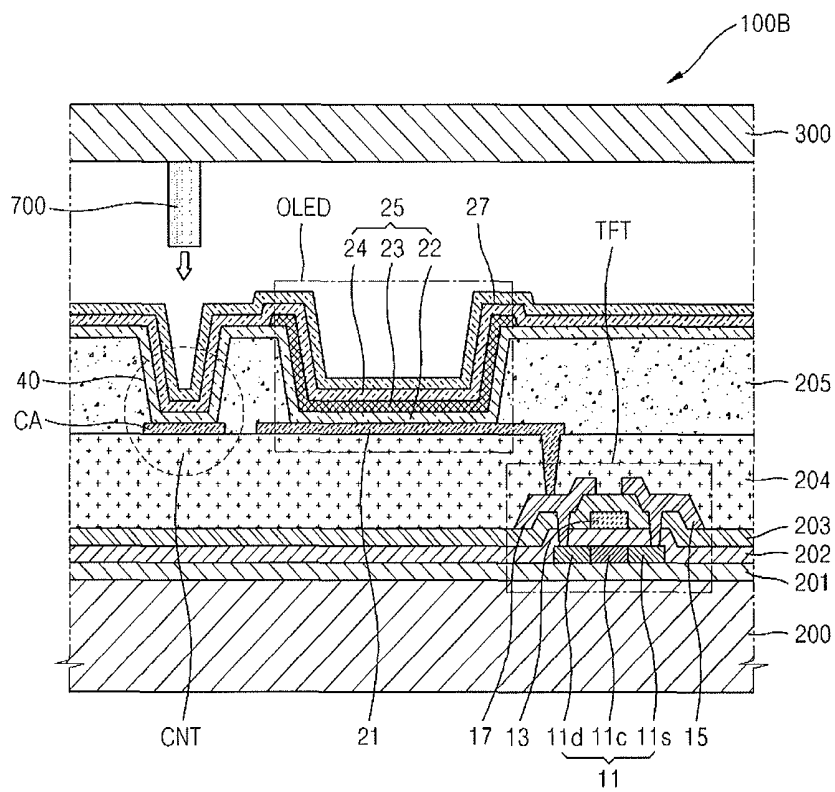


FIG. 7



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ORGANIC LIGHT EMITTING DISPLAY APPARATUS

CROSS-REFERENCE TO RELATED APPLICATION

Korean Patent Application No. 10-2013-0069955, filed on Jun. 18, 2013, in the Korean Intellectual Property Office, and entitled, "Organic Light Emitting Display Apparatus," is incorporated by reference herein in its entirety.

BACKGROUND

1. Field

One or more embodiments described herein relate to a display apparatus.

2. Description of the Related Art

An organic light emitting display apparatus is considered to be one of the next-generation display apparatuses because of its wide viewing angle, a high contrast, and fast response speed. An organic light emitting display apparatus may include an organic layer including an emission layer between first and second electrodes.

SUMMARY

An organic light emitting display apparatus may include a lower substrate including a light emitting device having an organic emission layer between first and second electrodes, and an auxiliary electrode under and electrically connected to the second electrode; and an upper substrate including an embossing member contacting the second electrode, wherein the embossing member is coupled to the upper substrate to face the lower substrate.

The light emitting device may further include an organic functional layer disposed between at least one of the first electrode or the second electrode and the organic emission layer, the organic functional layer extending outside an area where the auxiliary electrode contacts the second electrode. The organic functional layer may include at least one of a hole injection layer, a hole transport layer, an electron transport layer, or an electron injection layer.

The embossing member may directly contact the auxiliary electrode, to apply a pressure to cause the auxiliary electrode to electrically connect to the second electrode. The auxiliary electrode and the second electrode may directly contact each other. The embossing member may contact the second electrode at a location above the second electrode. The auxiliary electrode and the second electrode may contact one another through a break area in the organic functional layer.

The embossing member may include an organic insulating material. The embossing member may include a first pattern which includes an organic insulating material and a second pattern which includes a conductive material on the first pattern.

The lower substrate may include a thin film transistor electrically connected to the first electrode of the light emitting device.

The auxiliary electrode may be at a same level as a conductive layer configuring the thin film transistor. The auxiliary electrode may be at a same level as the first electrode of the light emitting device.

An organic light emitting display apparatus may include a first electrode on a lower substrate; a second electrode facing the first electrode; an organic emission layer between the first and second electrodes and an organic functional layer between at least one of the first electrode or second electrode

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and the organic emission layer; an auxiliary electrode electrically connected to the second electrode; and an embossing member coupled to an upper substrate which faces the lower substrate, wherein the embossing member contacts at least one of the auxiliary electrode or the second electrode.

The organic functional layer may include at least one of a hole injection layer, a hole transport layer, an electron transport layer, or an electron injection layer.

The embossing member may directly contact the auxiliary electrode, and the auxiliary electrode may electrically connect to the second electrode based on the direct contact between the embossing member and the auxiliary electrode.

The auxiliary electrode may electrically connect to the second electrode based on direct contact between the auxiliary electrode and the second electrode, and wherein the embossing member contacts the second electrode at a location above the second electrode. The embossing member includes an organic insulating material. The embossing member may include a first pattern including an organic insulating material and a second pattern including a conductive material on the first pattern. The organic functional layer may be located outside an area where the auxiliary electrode contacts the second electrode. The auxiliary electrode and the second electrode may contact one another through a break area in the organic functional layer.

BRIEF DESCRIPTION OF THE DRAWINGS

Features will become apparent to those of skill in the art by describing in detail exemplary embodiments with reference to the attached drawings in which:

FIG. 1 illustrates an embodiment of an organic light emitting display apparatus;

FIG. 2 illustrates a contact between a cathode and an auxiliary electrode in the apparatus of FIG. 1;

FIGS. 3 and 4 illustrate examples of an embossing member in FIG. 2;

FIG. 5 illustrates another embodiment of a contact between a cathode and an auxiliary electrode of an organic light emitting display apparatus;

FIG. 6 illustrates a cross-sectional view of another embodiment of an organic light emitting display apparatus; and

FIG. 7 illustrates a cross-sectional view of another embodiment of an organic light emitting display apparatus.

DETAILED DESCRIPTION

Example embodiments are described more fully hereinafter with reference to the accompanying drawings; however, they may be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey exemplary implementations to those skilled in the art.

In the drawing figures, the dimensions of layers and regions may be exaggerated for clarity of illustration. It will also be understood that when a layer or element is referred to as being "on" another layer or substrate, it can be directly on the other layer or substrate, or intervening layers may also be present. Further, it will be understood that when a layer is referred to as being "under" another layer, it can be directly under, and one or more intervening layers may also be present. In addition, it will also be understood that when a layer is referred to as being "between" two layers, it can be the only layer between the two layers, or one or more intervening layers may also be present. Like reference numerals refer to like elements throughout.

FIG. 1 illustrates an embodiment of an organic light emitting display apparatus 100 which includes auxiliary electrodes CA around anode electrodes AD on a lower substrate. The auxiliary electrodes CA may be formed at the same layer as the anode electrode AD or at a different layer from the anode electrode AD.

The auxiliary electrodes CA are formed as gratings. However, the auxiliary electrodes CA may have a different shape or arrangement in other embodiments, provided the auxiliary electrode CA is electrically separated from the anode electrode AD and electrically connected to a cathode electrode, which may serve as a common electrode.

For example, the auxiliary electrode CA may be formed in a zig-zag pattern or a stripe pattern in a column direction or a row direction. In addition, a width of the auxiliary electrode CA may vary, for example, according to a size of a pixel, and/or a density or a size of the auxiliary electrode CA may vary depending on pixel areas and/or other panel size requirements. If the auxiliary electrode CA is formed at a different layer from the anode electrode AD, the auxiliary electrode CA may partially overlap with the anode electrode AD.

In a top emission-type apparatus, a cathode electrode is deposited on an entire surface using an open mask and is formed to have a small thickness with an optical transmittance. In this case, a voltage drop (IR drop) may occur as a result of high surface resistance. Accordingly, a driving voltage may increase or a driving voltage margin may decrease, thereby degrading a long range uniformity (LRU).

According to one or more embodiments, the cathode electrode and the auxiliary electrode CA are electrically connected to each other, in order to reduce IR drop at the cathode electrode. Also, the auxiliary electrode CA may contact the cathode electrode with a predetermined interval or spacing.

FIG. 2 illustrates one embodiment for establishing contact between the cathode electrode and the auxiliary electrode. Referring to FIG. 2, the auxiliary electrode CA is formed on a lower substrate 200, and a part of the auxiliary electrode CA is exposed by an opening OP in a contact area CNT. One or more contact areas CNT may be formed. Also, one or more insulating layers 210 and 220 may be formed between the lower substrate 200 and the cathode electrode CD. An organic layer 230 and the cathode electrode CD may be sequentially formed in the opening OP of the auxiliary electrode CA. The organic layer 230 may include at least one of a hole injection layer (HIL), a hole transport layer (HTL), an electron transport layer (ETL), or an electron injection layer (EIL).

In addition, an embossing member or surface 700 is formed on a surface of an upper substrate 300, which faces the lower substrate 200. The embossing member 700 is formed on a location corresponding to the contact area CNT of the lower substrate 200.

FIGS. 3 and 4 are diagrams showing examples of the embossing member 700 shown in FIG. 2. As shown in FIG. 3, the embossing member 700 may be formed by depositing an insulating material, for example, a photo-resistor on a surface of the upper substrate 300 and patterning the photo-resistor.

As shown in FIG. 4, the embossing member 700 may include a first pattern 700a that is formed of an insulating material, for example, a photo-resistor on the surface of the upper substrate 300, and a second pattern 700b formed of a conductive material, for example, metal on the first pattern 700a. The first pattern 700a and the second pattern 700b may be formed, for example, by depositing the insulating material and the conductive material sequentially and etching the insulating material and the conductive material simultaneously.

Alternatively, the insulating material may be deposited and patterned to form the first pattern 700a, and the conductive

material may be patterned so as to remain on the first pattern 700a only to form the second pattern 700b. The second pattern 700b may have a thickness that is greater than a thickness of the organic layer 230. The second pattern 700b may be formed to have a single-layered structure or a multi-layered structure by using one or more conductive materials, for example, may have a triple-layered structure including Mo/Al/Mo. When the embossing member 700 includes the second pattern 700b, contact between the cathode electrode CD and the auxiliary electrode CA may be ensured.

The lower substrate 200 and the upper substrate 300 may be bonded to each other by a sealing member. The embossing member 700, formed on the upper substrate 300, physically presses the contact area CNT on the lower substrate 200 to breakdown the organic layer 230 having a weak mechanical strength, to thereby establish direct contact between the cathode electrode CD and the auxiliary electrode CA. When the cathode electrode CD and the auxiliary electrode CA may be electrically connected to each other, a surface resistance of the cathode electrode CD (e.g., formed as a thin film) may be reduced. Accordingly, a driving voltage may be reduced, which may thereby reduce power consumption.

FIG. 5 illustrates another embodiment for establishing contact between the cathode electrode CD and the auxiliary electrode CA. Referring to FIG. 5, the auxiliary electrode CA is formed on the lower substrate 200, and the auxiliary electrode CA is partially exposed by an opening OP in a contact area CNT. One or more contact areas CNT may be formed. One or more insulating layers 210 and 220 may be formed between the lower substrate 200 and the cathode electrode CD. An organic layer 230 and the cathode electrode CD are sequentially formed in the opening OP of the auxiliary electrode CA. The organic layer 230 may include at least one of an HIL, an HTL, an ETL, or an EIL.

In addition, an embossing member 700 is formed on a surface of the upper substrate 300, which faces the lower substrate 200. The embossing member 700 is formed on a location corresponding to the contact area CNT of the lower substrate 200.

The lower substrate 200 and the upper substrate 300 may be bonded to each other by a sealing member. The embossing member 700, formed on the upper substrate 300, presses the contact area CNT of the lower substrate 200 to breakdown the organic layer 230 and the cathode electrode CD to directly contact the auxiliary electrode CA. Accordingly, the cathode electrode CD and the auxiliary electrode CA may be electrically connected to each other via the embossing member 700. As a result, surface resistance of the cathode electrode CD (e.g., formed as a thin film) may be reduced. Therefore, a driving voltage may be reduced, to thereby lower power consumption. In this case, the embossing member 700 may include a conductive material at a portion contacting the auxiliary electrode CA as shown in FIG. 4.

FIG. 6 illustrates a cross-sectional view of another organic light emitting display apparatus 100A. Referring to FIG. 6, a thin film transistor TFT and an organic light emitting device (OLED) are formed on a lower substrate 200 of the organic light emitting display apparatus 100A. The TFT includes an active layer 11, a gate electrode 13, and source/drain electrodes 15 and 17. The OLED includes a first electrode 21, an intermediate layer 25, and a second electrode 27.

First, the active layer 11 is formed on the lower substrate 200. The lower substrate 200 may be formed of a transparent glass material including SiO₂ mainly. Alternatively, the lower substrate 200 may be formed of various other materials, for example, a transparent plastic material, or a metal material.

An auxiliary layer **201** may be selectively formed on the lower substrate **200**. The auxiliary layer may be a barrier layer, a blocking layer, and/or a buffer layer for preventing diffusion of impurity ions, infiltration of moisture or external air, and for surface planarization.

The active layer **11** may be formed by patterning a polysilicon layer. The active layer **11** may further include semiconductor and may include ion impurities by a doping process. Also, the active layer **11** may be formed of an oxide semiconductor. The active layer **11** includes source/drain regions **11s** and **11d** doped by n-type or p-type impurities to correspond to opposite sides of the gate electrode **13**, and a channel region **11c** between the source and drain regions **11s** and **11d**.

A first insulating layer **202** and the gate electrode of the TFT are formed on the lower substrate **200**, on which the active layer **11** is formed.

The first insulating layer **202** may be formed of an inorganic insulating layer such as SiN_x or SiO_x or an organic insulating layer on an entire surface of the lower substrate **200** using a plasma enhanced chemical vapour deposition (PECVD) method, an atmospheric pressure CVD (APCVD) method, and a low pressure CVD (LPCVD) method. The first insulating layer **202** may be disposed between the active layer **11** and the gate electrode **13** of the TFT to function as a gate insulating layer of the TFT.

The gate electrode **13** is formed to correspond to a center portion of the active layer **11**, and may be formed of various conductive materials. For example, the gate electrode **13** may be formed to have a single-layered or a multi-layered structure including one or more materials selected from M Ag, Mg, Al, Pt, Pd, Au, Ni, Nd, Ir, Cr, Li, Ca, Mo, Ti, W, MoW, and Cu.

A second insulating layer **203** and the source/drain electrodes **15** and **17** of the TFT are formed on the lower substrate **200** on which the gate electrode **13** is formed.

The second insulating layer **203** may be formed of the same inorganic insulating material as that of the first insulating layer **202** on the entire surface of the lower substrate **200**. The second insulating layer **203** functions as an interlayer dielectric between the gate electrode **13** and the source/drain electrodes **15** and **17** of the TFT.

Alternatively, the second insulating layer **203** may be formed of one or more organic insulating materials selected from the group consisting of polyimide, polyamide, acryl resin, benzocyclobutene, and phenol resin, as well as the inorganic insulating material, or may be formed to include an organic insulating material and an inorganic insulating material alternately. Contact holes exposing the source/drain regions **11s** and **11d** respectively are formed in the first insulating layer **202** and the second insulating layer **203**.

The source/drain electrodes **15** and **17** may be formed of the same conductive material as that of the gate electrode **13** on the second insulating layer **203**. In other embodiments, other conductive materials may be used. The source/drain electrodes **15** and **17** are electrically connected to the source/drain regions **11s** and **11d** of the active layer **11** via the contact holes formed in the first and second insulating layers **202** and **203**.

In addition, the auxiliary electrode CA may be formed at the same layer as that of the source/drain electrodes **15** and **17** by a patterning process. In one embodiment, the auxiliary electrode CA may be formed around or adjacent the pixel electrode **21** in order to prevent an IR drop of the cathode electrode CD that is formed later. The auxiliary electrode CA may be formed of a material that is the same as or different

from the source/drain electrodes **15** and **17**. The auxiliary electrode CA may include a triple-layered structure including, for example, Mo/Al/Mo.

A third insulating layer **204** is formed on the source/drain electrode **15** and **17** and the auxiliary electrode CA. The third insulating layer **204** may be formed of one or more organic insulating materials selected from the group consisting of polyimide, polyamide, acryl resin, benzocyclobutene, and phenol resin by using a spin coating method. Alternatively, the third insulating layer **204** may be formed of an inorganic insulating material selected from SiO_2 , SiN_x , Al_2O_3 , CuO_x , Tb_4O_7 , Y_2O_3 , Nb_2O_5 , and Pr_2O_3 , as well as the organic insulating material.

Also, the third insulating layer **204** may be formed to have a multi-layered structure including the organic insulating material and the inorganic insulating material alternately. The third insulating layer **204** performs as a planarizing layer for protecting and planarizing the TFT.

The first electrode **21** is formed on the third insulating layer **204**. The first electrode **21** may have a double-layered structure including a lower layer formed of a metal material having high reflectivity, for example, Ag, Mg, Al, Pt, Pd, Au, Ni, Nd, Ir, Cr, Li, Ca, and a compound thereof, and an upper layer formed of a transparent conductive material having a relatively high work function, for example, indium tin oxide (ITO), indium zinc oxide (IZO), ZnO, IGO, or In_2O_3 .

The first electrode **21** is electrically connected to one of the source/drain electrodes **15** and **17** via the contact hole.

A fourth insulating layer **205** including an opening that exposing a part of the first electrode **21** is formed on the first electrode **21**. The fourth insulating layer **205** functions as a pixel define layer (PDL). The fourth insulating layer **205** may be formed of one or more organic insulating materials selected from the group consisting of polyimide, polyamide, acryl resin, benzocyclobutene, and phenol resin by using a spin coating method. Alternatively, the fourth insulating layer **205** may be formed of an inorganic insulating material selected from SiO_2 , SiN_x , Al_2O_3 , CuO_x , Tb_4O_7 , Y_2O_3 , Nb_2O_5 , and Pr_2O_3 , as well as the organic insulating material. Also, the fourth insulating layer **205** may be formed to have a multi-layered structure including the organic insulating material and the inorganic insulating material alternately.

In addition, the third insulating layer **204** and the fourth insulating layer **205** on the auxiliary electrode CA are removed in the contact area CNT to expose a part of the auxiliary electrode CA. The intermediate layer **25** and the second electrode **27** are sequentially formed on the first electrode **21**. The intermediate layer **25** includes a first organic functional layer **22**, an organic emission layer **23**, and a second organic functional layer **24**. Locations of the first organic functional layer **22** and the second organic functional layer **24** may be exchanged according to functions of the first and second electrodes **21** and **27**. One of the first organic functional layer **22** and the second organic functional layer **24** may be omitted. The first electrode **21** may function as an anode electrode and the second electrode **27** may function as a cathode electrode.

The first organic functional layer **22** may include at least one of a hole injection layer (HIL) and a hole transport layer (HTL), and is a common layer that is formed on the entire surface of the lower substrate **200**.

The HIL may be formed to have a predetermined thickness so that holes may be injected easily, and the thickness may vary depending on materials forming the other layers. The HTL may be formed of phthalocyanine compound such as copper phthalocyanine, or TCTA, m-MTDATA, or m-MT-DAPB that is star-bust type amine.

The HTL has high hole mobility to transport the holes easily, and a deposition condition and a coating condition of the HTL may vary depending on compounds that are used; however, may be selected from the conditions that are nearly the same as those of forming the HIL. The HTL may be formed of N,N'-bis(3-methylphenyl)-N,N'-diphenyl-[1,1-biphenyl]-4,4'-diamine (TPD), N,N'-di(naphthalene-1-yl)-N,N'-diphenyl benzidine (α -NPD), and the like.

The organic emission layer **23** is a patterned layer formed on the first electrode **21**. The organic emission layer **23** may be formed of a low molecular weight or a high molecular weight organic material. If the organic emission layer **23** emits red light, green light, and blue light, the organic emission layer **23** may be patterned as a red light emission layer, a green light emission layer, and a blue light emission layer.

If the organic emission layer **23** emits white light, the organic emission layer **23** may have a multi-layered structure in which the red light emission layer, the green light emission layer, and the blue light emission layer are stacked. Alternatively, the organic emission layer **23** may have a single-layered structure including a red light emission material, a green light emission material, and a blue light emission material for emitting white light.

The organic emission material may include various light emitting materials, for example, oxadiazole dimer dyes (Bis-DAPDXP), spiro compounds (Spiro-DPVB, Spiro-6P), triarylamine compounds, bis(styryl)amine (DPVB, DSA), BCzVBi (4,4'-bis(9-ethyl-3-carbazole vinylene)-1,1'-biphenyl), perylene, TPBe (2,5,8,11-tetra-tert-butylperylene), BCzVB (9H-carbazole-3,3'-(1,4-phenylene-di-2,1-ethenediyl)bis[9-ethyl-(9C)]), DPAVB (4,4-bis[4-(di-p-tolyl amino)styryl]biphenyl), DPAVB (4-(di-p-tolyl amino)-4'-[(di-p-tolyl amino)styryl]stilbene), BDAVB (4,4'-bis[4-(diphenyl amino)styryl]biphenyl), FIrPic (bis(3,5-difluoro-2-(2-pyridyl)phenyl-(2-carboxy pyridyl)iridium III)), and the like (blue light); coumarin 6(3-(2-benzothiazolyl)-7-(diethyl amino)coumarin), C545T (2,3,6,7-tetra hydro-1,1,7,7-tetra methyl-1H,5H,11H-10-(2-benzothiazolyl) quinolizino[9,9a,1gh]coumarin), DMQA (N,N'-dimethyl-quinacridone), Ir(ppy)₃ (tris(2-phenyl pyridine)iridium (III)), and the like (green light); tetraphenylanthracene (Rubrene), Ir(piq)₃ (tris(1-phenyl isoquinoline)iridium(III)), bis (2-benzo[b] thiophene-2-yl-pyridine) (acetyl acetate)iridium (III) (Ir (btp)₂(acac)), tris(dibenzoylmethane) phenanthroline europium (III) (Eu(dbm)₃(phen)), tris[4,4'-di-tert-butyl-(2,2')-bipyridine]ruthenium (III) complex (Ru(dtb-bpy)₃*2 (PF₆)), DCM1, DCM2, Eu(TTA)₃ (europium(thenoyltrifluoroacetone)₃), CJTB (butyl-6-(1,1,7,7-tetramethyljulolidyl-9-enyl)-4H-pyran), and the like (red light).

Also, the light emitting material may be a high molecular light emitting material, for example, aromatic compounds including a polymer such as phenylene-based polymer, phenylene vinylene-based polymer, thiophene-based polymer, fluorine-based polymer, or spiro-fluorene-based polymer, and nitrogen; however, it is not limited thereto.

If necessary, the organic emission layer may include a light emitting host and a light emitting dopant. The light emitting dopant may include the above described light emitting material, and the light emitting host may include a fluorescent light emitting host material or a phosphorous light emitting host material. The fluorescent light emitting host material may be Alq₃, 9,10-di(naphthyl-2-yl)anthracene (AND), 2-tert-butyl-9,10-bis-((β -naphthyl)-anthracene (TBADN), 4,4'-Bis(2,2-diphenylvinyl)-1,1'-biphenyl (DPVB), 4,4'-Bis[2,2-di(4-methylphenyl)-ethen-1-yl]biphenyl (p-DMDPVB), Tert(9,9-diarylfuorene)s (TDAF), 2-(9,9'-spirobifluorene-2-yl)-9,9'-spirobifluorene (BSDF), 2,7-bis(9,9'-spirobifluorene-2-

yl)-9,9'-spirobifluorene (TSDF), Bis(9,9-diarylfuorene)s (BDAF), or 4,4'-bis(2,2-diphenyl-ethene-1-yl)-4,4'-di-(tert-butyl)phenyl (p-TDPVB), and the phosphorous light emitting host material may be 1,3-bis(carbazol-9-yl)benzene (mCP), 1,3,5-Tris(carbazol-9-yl)benzene (tCP), 4,4',4"-Tris(carbazol-9-yl)triphenylamine (TcTa), 4,4'-N,N'-dicarbazole-biphenyl (CBP), 4,4'-bis(9-carbazolyl)-2,2'-dimethylbiphenyl (CBDP), 4,4'-Bis(carbazol-9-yl)-9,9-dimethylfluorene (DMFL-CBP), 4,4'-bis(carbazole-9-yl)-9,9-bis(9-phenyl-9H-carbazole)fluorene (FL-4CBP), 4,4'-bis(carbazol-9-yl)-9,9-ditolylfluorene (DPFL-CBP), or 9,9-bis(9-phenyl-9H-carbazol)fluorene (FL-2CBP). The dopant material of the organic emission layer may be 1,4'-bis[4-(di-p-tolylamino)styryl]biphenyl (DPAVB), 9,10-di-(2-naphthyl)anthracene (ADN), or 2-tert-butyl-9,10-di(naphth-2-yl)anthracene (TBADN).

The second organic functional layer **24** may include at least one of an electron transport layer (ETL) and an electron injection layer (EIL), and is a common layer formed on the entire surface of the lower substrate **200**. The ETL provide sufficient electron transport, and may be formed of Alq₃. The EIL performs injection of electrons, and may be formed of LiF, NaCl, CsF, Li₂O, BaO, or Liq.

The first and second organic functional layers **22** and **24** are common layers that are formed on the auxiliary electrode CA in the contact area CNT.

The second electrode **27** may be formed on the entire surface of the lower substrate **200** as a common electrode, and faces the first electrode **21**. The second electrode **27** is formed of a thin transparent conductive material for performing top emission. Also, the second electrode **27** may be formed as a double-layered structure including a semi-transparent metal layer including metal having a small work function, that is, Ag, Mg, Al, Pt, Pd, Au, Ni, Nd, Ir, Cr, Li, Ca, and a compound thereof, and a transparent conductive layer formed of ITO, IZO, ZnO, or In₂O₃ on the semi-transparent metal layer.

In addition, the embossing member **700** is formed on a surface of the upper substrate **300**. The upper substrate **300** may be formed of various materials, for example, a transparent glass material including SiO₂ mainly, a transparent plastic material, or a metal material, like the lower substrate **200**.

The embossing member **700** may have a structure shown in FIG. 3 or FIG. 4, and one or more embossing members **700** may be formed to correspond to the contact area CNT. The embossing member **700** may be formed to have a sufficient height to press the contact area CNT, so that the second electrode **27** and the auxiliary electrode CA may be electrically connected to each other.

When the lower substrate **200** and the upper substrate **300** are bonded to each other, the embossing member **700** physically presses the second electrode **27** and the first and second organic functional layers **22** and **24** in the contact area CNT. As a result, the second electrode **27** and the auxiliary electrode CA contact each other as shown in FIG. 2, or the embossing member **700** directly contacts the auxiliary electrode CA as shown in FIG. 5, so that the second electrode **27** and the auxiliary electrode CA may be electrically connected to each other.

FIG. 7 illustrates another embodiment of an organic light emitting display apparatus **100B**, which is different from the organic light emitting display apparatus **100A** shown in FIG. 6 in that the auxiliary electrode CA is formed at the same layer as the first electrode **21**.

Referring to FIG. 7, the TFT is formed on the lower substrate **200**. The TFT includes the active layer **11** including the source/drain regions **11s** and **11d**, and the channel region **11c**

between the source/drain regions **11s** and **11d**, the gate electrode **13**, and the source/drain electrodes **15** and **17**.

The third insulating layer **204** is formed on the TFT, and an organic light emitting diode (OLED) that is electrically connected to the TFT is formed. The OLED includes the first electrode **21**, the intermediate layer **25**, and the second electrode **27**.

The first electrode **21** and the auxiliary electrode CA are formed on the third insulating layer **204**. The auxiliary electrode CA is formed around the first electrode **21** to be electrically insulated from the first electrode **21**, and may be formed of a material that is the same as or different from that of the first electrode **21**.

The first electrode **21** is electrically connected to one of the source and drain electrodes **15** and **17** via the contact hole. The first electrode **21** may have a double-layered structure including a lower layer formed of a metal material, having high reflectivity, for example, Ag, Mg, Al, Pt, Pd, Au, Ni, Nd, Ir, Cr, Li, Ca, and a compound thereof, and an upper layer formed of a transparent conductive material having a relatively high work function, for example, ITO, IZO, ZnO, IGO, or In_2O_3 .

The fourth insulating layer **205** is formed and patterned on the first electrode **21** and the auxiliary electrode CA to form openings that expose a part of the first electrode **21** and a part of the auxiliary electrode CA.

The intermediate layer **25** and the second electrode **27** are sequentially formed in the opening that exposing the first electrode **21**. The intermediate layer **25** includes the first organic functional layer **22**, the organic emission layer **23**, and the second organic functional layer **24**. The first and second organic functional layer **22** and **24**, and the second electrode **27** are formed on the exposed auxiliary electrode CA in the contact area CNT.

The embossing member **700** is formed on a surface of the upper substrate **300**. The embossing member **700** may have a structure shown in FIG. 3 or FIG. 4, and one or more embossing members **700** may be formed to correspond to the contact area CNT. The embossing member **700** may be formed to have a sufficient height to press the contact area CNT, so that the second electrode **27** and the auxiliary electrode CA may be electrically connected to each other.

When the lower substrate **200** and the upper substrate **300** are bonded to each other, the embossing member **700** physically presses the second electrode **27** and the first and second organic functional layers **22** and **24** in the contact area CNT. As a result, the second electrode **27** and the auxiliary electrode CA contact each other as shown in FIG. 2. Alternatively, the embossing member **700** may directly contact the auxiliary electrode CA as shown in FIG. 5, so that the second electrode **27** and the auxiliary electrode CA may be electrically connected to each other.

In the above embodiments, the auxiliary electrode is formed at the same layer as the source/drain electrodes or the pixel electrode. In alternative embodiments, the auxiliary electrode may be formed at the same layer as the gate electrode or the active layer, or may be formed in other layers.

In the aforementioned embodiments, a coplanar type TFT is described as an example. In other embodiments, various other types of TFTs may be used, including but not limited to a staggered-type, an inverted staggered type, and an inverted coplanar type TFT.

In a light emitting device where the second electrode is a common electrode, i.e., supplies the same voltage to all pixels, a voltage drop (IR drop) occurs due to high specific

resistance of the second electrode. As a result, voltages of different levels are applied to the pixels based on to their respective locations.

By way of summation and review, embodiments relate to an organic light emitting display apparatus suitable for mass production of large-sized substrates, and capable of reducing voltage drop in an electrode to which a driving voltage is applied.

According to one or more embodiments, an auxiliary electrode is formed under the cathode electrode. The cathode electrode and the auxiliary electrode are then electrically connected to each other via the contact hole. Such an arrangement may be suitable fabricating an enlarged display apparatus, when compared to the case where the auxiliary electrode is directly formed on the cathode electrode by using a fine metal mask (FMM) process.

According to one or more embodiments, the auxiliary electrode contacting the cathode electrode may be used to prevent electrical characteristics of a top emission-type display apparatus from degrading. The organic material formed on the auxiliary electrode may be removed using the embossing member formed on the upper substrate to prevent the contact defects due to the organic material. Thus, an electrical path between the auxiliary electrode and the cathode electrode may be easily formed. Accordingly, the embodiments may be suitable for mass production of large sized substrates. In addition, the IR drop of the electrode to which the driving voltage is applied may be reduced, to improve unevenness of brightness. Thus, a display apparatus of high resolution may be realized.

According to one or more embodiments, the embossing member may be formed on the upper substrate to correspond to the contact area where the second electrode and the auxiliary electrode on the lower substrate are electrically connected to each other. This may ensure electrical connection between the second electrode and the auxiliary electrode. These embodiments are suitable for the mass production of a large sized substrate, and also an organic light emitting display apparatus of high resolution may be manufactured.

Example embodiments have been disclosed herein, and although specific terms are employed, they are used and are to be interpreted in a generic and descriptive sense only and not for purpose of limitation. In some instances, as would be apparent to one of ordinary skill in the art as of the filing of the present application, features, characteristics, and/or elements described in connection with a particular embodiment may be used singly or in combination with features, characteristics, and/or elements described in connection with other embodiments unless otherwise specifically indicated. Accordingly, it will be understood by those of skill in the art that various changes in form and details may be made without departing from the spirit and scope of the present invention as set forth in the following claims.

What is claimed is:

1. An organic light emitting display apparatus, comprising: a first substrate including a light emitting device having an organic emission layer between first and second electrodes, and an auxiliary electrode directly contacting the second electrode; and

a second substrate including an embossing member at a surface facing the first substrate, wherein the embossing member contacts the second electrode.

2. The apparatus as claimed in claim 1, wherein the light emitting device further comprises an organic functional layer disposed between at least one of the first electrode or the second electrode and the organic emission layer, the organic

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functional layer extending outside an area where the auxiliary electrode contacts the second electrode.

3. The apparatus as claimed in claim 2, wherein the organic functional layer comprises at least one of a hole injection layer, a hole transport layer, an electron transport layer, or an electron injection layer.

4. The apparatus as claimed in claim 1, wherein the embossing member directly contacts the auxiliary electrode.

5. The apparatus as claimed in claim 1, wherein the embossing member directly contacts a top surface of the second electrode.

6. The apparatus as claimed in claim 2, wherein the auxiliary electrode and the second electrode contact one another through a break area in an organic functional layer.

7. The apparatus as claimed in claim 1, wherein the embossing member includes an organic insulating material.

8. The apparatus as claimed in claim 1, wherein the embossing member comprises a first pattern which includes an organic insulating material and a second pattern which includes a conductive material on the first pattern.

9. The apparatus as claimed in claim 1, wherein the first substrate comprises a thin film transistor electrically connected to the first electrode of the light emitting device.

10. The apparatus as claimed in claim 9, wherein the auxiliary electrode is at a same level as a conductive layer configuring the thin film transistor.

11. The apparatus of claim 9, wherein the auxiliary electrode is at a same level as the first electrode of the light emitting device.

12. An organic light emitting display apparatus, comprising:
 a first electrode on a first substrate;
 a second electrode facing the first electrode;
 an organic emission layer between the first and second electrodes and an organic functional layer between at least one of the first electrode or second electrode and the organic emission layer;
 an auxiliary electrode in direct contact with the second electrode; and
 an embossing member coupled to a surface of a second substrate which faces the lower substrate, wherein the

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embossing member contacts at least one of the auxiliary electrode or the second electrode of the first substrate.

13. The apparatus as claimed in claim 12, wherein the organic functional layer comprises at least one of a hole injection layer, a hole transport layer, an electron transport layer, or an electron injection layer.

14. An organic light emitting diode apparatus, comprising:
 a first electrode on a lower substrate;

a second electrode facing the first electrode;

an organic emission layer between the first and second electrodes and an organic functional layer between at least one of the first electrode or second electrode and the organic emission layer;

an auxiliary electrode electrically connected to the second electrode; and

an embossing member coupled to an upper substrate which faces the lower substrate, wherein the embossing member directly contacts the auxiliary electrode.

15. The apparatus as claimed in claim 12, wherein the embossing member directly contacts a top surface of the second electrode.

16. The apparatus as claimed in claim 12, wherein the embossing member includes an organic insulating material.

17. The apparatus as claimed in claim 12, wherein the embossing member comprises a first pattern including an organic insulating material and a second pattern including a conductive material on the first pattern.

18. The apparatus as claimed in claim 12, wherein the organic functional layer is located outside of an area where the auxiliary electrode contacts the second electrode.

19. The apparatus as claimed in claim 18, wherein the auxiliary electrode and the second electrode contact one another through a break area in the organic functional layer.

20. The apparatus as claimed in claim 8, wherein the second pattern of the embossing member contacts at least one of the auxiliary electrode or the second electrode.

21. The apparatus as claimed in claim 17, wherein the second pattern of the embossing member contacts at least one of the auxiliary electrode of the second electrode.

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专利名称(译)	有机发光显示装置		
公开(公告)号	US9299950	公开(公告)日	2016-03-29
申请号	US14/071001	申请日	2013-11-04
[标]申请(专利权)人(译)	三星显示有限公司		
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IPC分类号	H01L27/32 H01L51/52		
CPC分类号	H01L51/525 H01L51/5221 H01L51/5228		
审查员(译)	VU , DAVID		
优先权	1020130069955 2013-06-18 KR		
其他公开文献	US20140367651A1		
外部链接	Espacenet USPTO		

摘要(译)

有机发光显示装置包括下基板和上基板。下基板包括发光器件，该发光器件在第一和第二电极之间具有有机发光层，并且辅助电极在第二电极下面并且电连接到第二电极。上基板包括与第二电极接触的压花构件。压花构件连接到上基板以面对下基板并施加压力以在辅助电极和第二电极之间建立电连接。

Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 142 days.